



	<h2>SI7884BDP-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI7884BDP-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 40V 58A PPAK SO-8</p> <p>Datenblätter:  SI7884BDP-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 27668 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7884BDP-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 40V 58A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	27668 pcs Stock
detaillierte Beschreibung	N-Channel 40V 58A (Tc) 4.6W (Ta), 46W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SO-8
Supplier Device-Gehäuse	PowerPAK® SO-8
Verlustleistung (max)	4.6W (Ta), 46W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	40V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	58A (Tc)
Rds On (Max) @ Id, Vgs	7.5 mOhm @ 16A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	77nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	3540pF @ 20V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7884BDP-T1-GE3CT

SI7884BDP-T1-GE3 ist neu im Original, Suche SI7884BDP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7884BDP-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7884BDP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 SI7884DP-T1 VISHAY SI7884DP-T1 VISHAY	 SI7884DP-T1-E3 VISHAY SI7884DP-T1-E3 VISHAY	 SI7884BDP VISHAY SI7884BDP VISHAY	 SI7884BDP-T1-E3 VISHAY VISHAY PQFN8
 SI7884DP VISHAY VISHAY QFN	 SI7882DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 12V 13A PPAK SO-8	 SI7884BDP-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 40V 58A PPAK SO-8	 SI7884BDP-T1-GE3 Vishay / Siliconix MOSFET N-CH 40V 58A PPAK SO-8

heiße Teile

Mehr

 SI7868ADP-T1-E3	 SI7868ADP-T1-GE3	 SI7868ADP-T1-GE3	 SI7868DP-T1	 SI7868DP-T1-E3
 SI7868DP-T1-GE3	 SI786LG-T1	 SI786LG-T1-E3	 SI7872DP	 SI7872DP-T1-E3
 SI7872DP-T1-E3	 SI7872DP-T1-GE3	 SI7872DP-T1-GE3	 SI7880ADP-T1-E3	 SI7880ADP-T1-E3
 SI7880ADP-T1-GE3	 SI7880ADP-T1-GE3	 SI7880DP-T1-GE3	 SI7882DP-T1-E3	 SI7882DP-T1-E3
 SI7882DP-T1-GE3	 SI7882DP-T1-GE3	 SI7884BDP	 SI7884BDP-T1-E3	 SI7884BDP-T1-E3
 SI7884BDP-T1-GE3	 SI7884DP-T1-E3	 SI7884DP-T1-GE3	 SI7886ADP-T1-E3	 SI7886ADP-T1-E3
 SI7886ADP-T1-GE3	 SI7886ADP-T1-GE3	 SI7886DP	 SI7886DP-T1	 SI7886DP-T1-E3
 SI7886DP-T1-GE3	 SI7888DP-T1-E3	 SI7888DP-T1-E3	 SI7888DP-T1-GE3	 SI7888DP-T1-GE3
 SI7892ADP-T1-E3	 SI7892ADP-T1-GE3	 SI7892ADP-T1-GE3.	 SI7892BDP-T1-E3	 SI7892BDP-T1-E3
 SI7892BDP-T1-GE3	 SI7892BDP-T1-GE3	 SI7892DP	 SI7892DP-T1	 SI7892DP-T1-E3

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